Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

March 2016

FGA50S110P

1100 V, 50 A Shorted-anode IGBT

Features

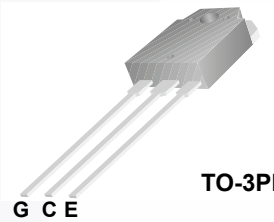
- Intrinsic Anti-parallel Diode for Soft-switching Applications
- High Switching Frequency Range 10 kHz to 50kHz
- High Temperature Stable Behavior (T_{jmax} = 175°C)
- Low Saturation Voltage Drop : $V_{CE(sat)}$ = 2.06 V @ I_C = 50 A
- Robust Pot Detection Noise Immunity
- RoHS Compliant (Pb-free lead plating)

General Description

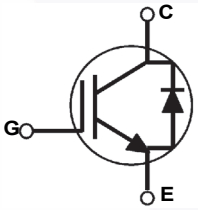
Using advanced field stop trench and shorted-anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for switching applications. This device is tailored to induction cooker and microwave oven.

Applications

- Induction Cooker, Rice-jar, and Microwave Oven
- Soft-switching Applications



TO-3PN



Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V_{CES}	Collector to Emitter Voltage		1100	V
V_{GES}	Gate to Emitter Voltage		±25	V
I_C	Collector Current	@ T_C = 25°C	50	A
	Collector Current	@ T_C = 100°C	30	A
$I_{CM\ (1)}$	Pulsed Collector Current		120	A
I_F	Diode Continuous Forward Current	@ T_C = 25°C	50	A
	Diode Continuous Forward Current	@ T_C = 100°C	30	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	300	W
	Maximum Power Dissipation	@ T_C = 100°C	150	W
T_J	Operating Junction Temperature		-55 to +175	°C
T_{stg}	Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case, Max	-	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	-	40	°C/W

Notes:

1: Limited by T_{jmax}

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA50S110P	FGA50S110P	TO-3PN	-	-	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
I_{CES}	Collector Cut-Off Current	V_{CE} = 1100 V, V_{GE} = 0 V	-	-	1	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	-	-	±500	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 50 mA, V_{CE} = V_{GE}	4.5	5.6	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 50 A, V_{GE} = 15 V T_C = 25°C	-	2.06	2.6	V
		I_C = 50 A , V_{GE} = 15 V T_C = 125°C	-	2.54	-	V
		I_C = 50 A, V_{GE} = 15 V, T_C = 175°C	-	2.7	-	V
V_{FM}	Diode Forward Voltage	I_F = 50 A, T_C = 25°C	-	1.96	2.6	V
		I_F = 50 A, T_C = 175°C	-	2.67	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	-	2056	-	pF
C_{oes}	Output Capacitance		-	47.8	-	pF
C_{res}	Reverse Transfer Capacitance		-	35.8	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 50 A, R_G = 10 Ω, V_{GE} = 15 V, Resistive Load, T_C = 25°C	-	24	-	ns
t_r	Rise Time		-	294	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	280	-	ns
t_f	Fall Time		-	95	-	ns
E_{on}	Turn-On Switching Loss		-	2240	-	uJ
E_{off}	Turn-Off Switching Loss		-	990	-	uJ
E_{ts}	Total Switching Loss		-	3230	-	uJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600 V, I_C = 50 A, R_G = 10 Ω, V_{GE} = 15 V, Resistive Load,, T_C = 175°C	-	24	-	ns
t_r	Rise Time		-	346	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	308	-	ns
t_f	Fall Time		-	184	-	ns
E_{on}	Turn-On Switching Loss		-	2640	-	uJ
E_{off}	Turn-Off Switching Loss		-	1820	-	uJ
E_{ts}	Total Switching Loss		-	4460	-	uJ
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 50 A, V_{GE} = 15 V	-	195	-	nC
Q_{ge}	Gate to Emitter Charge		-	15.4	-	nC
Q_{gc}	Gate to Collector Charge		-	99.9	-	nC

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

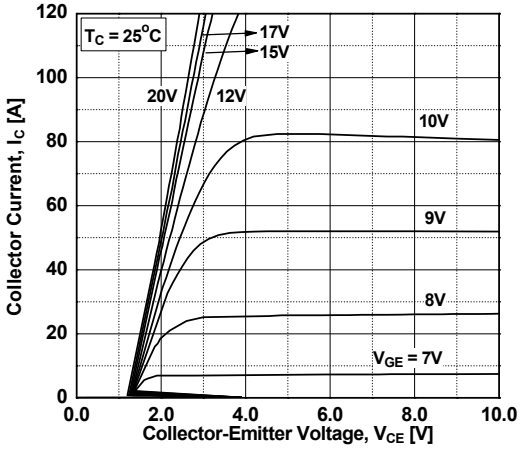


Figure 2. Typical Output Characteristics

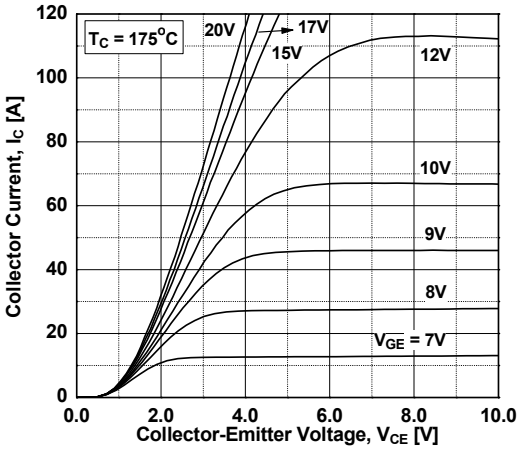


Figure 3. Typical Saturation Voltage Characteristics

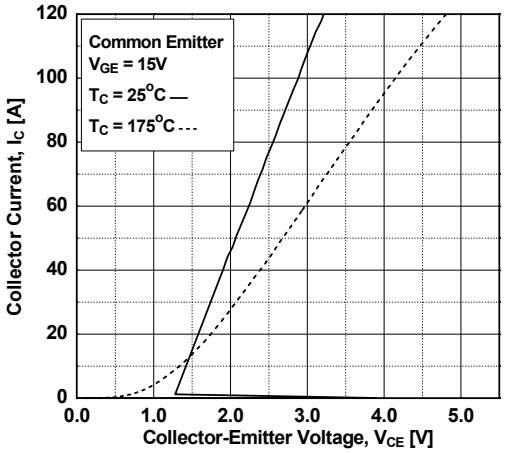


Figure 4. Transfer Characteristics

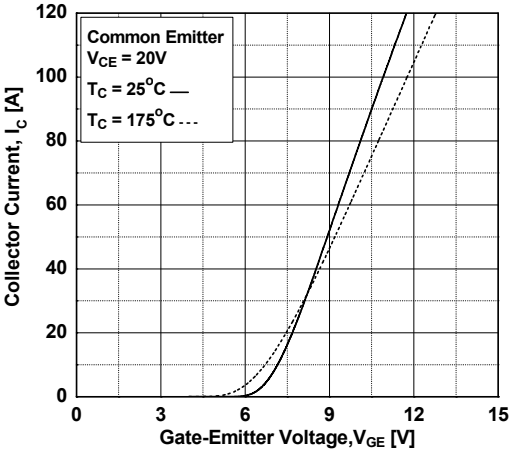


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

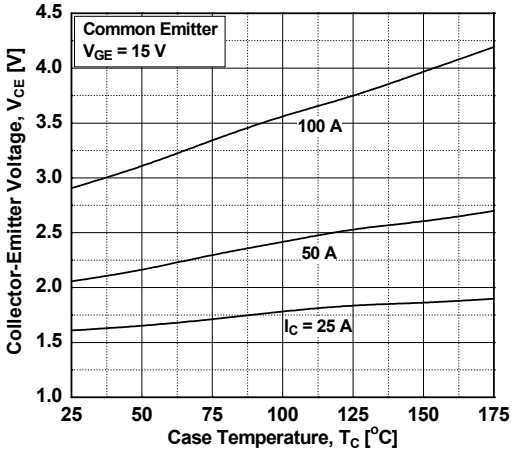
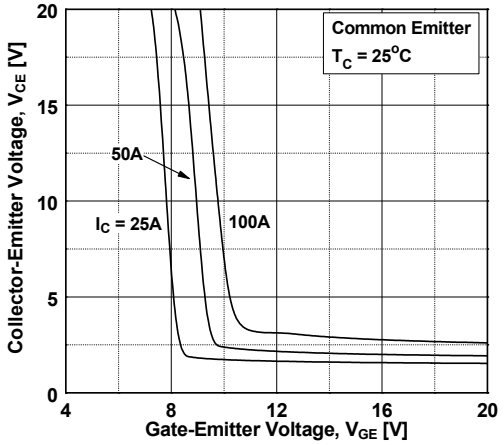


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

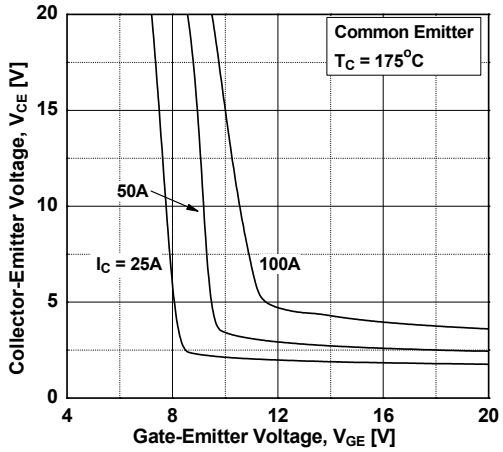


Figure 8. Capacitance Characteristics

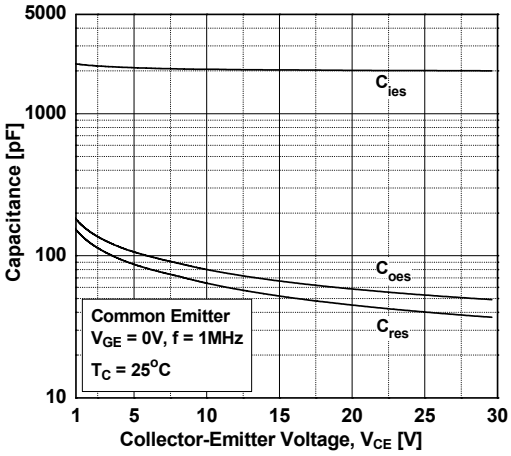


Figure 9. Gate charge Characteristics

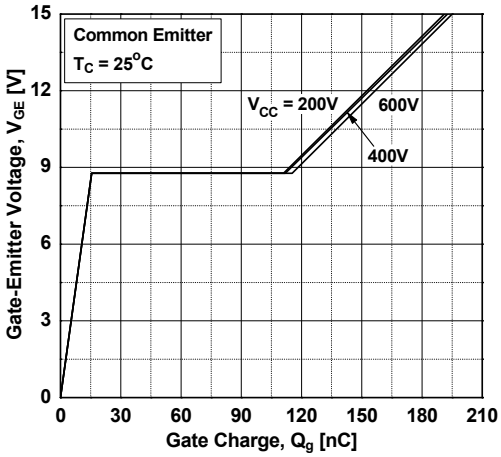


Figure 10. SOA Characteristics

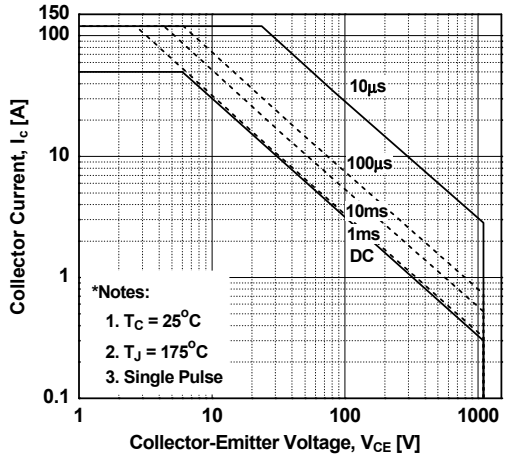


Figure 11. Turn-on Characteristics vs. Gate Resistance

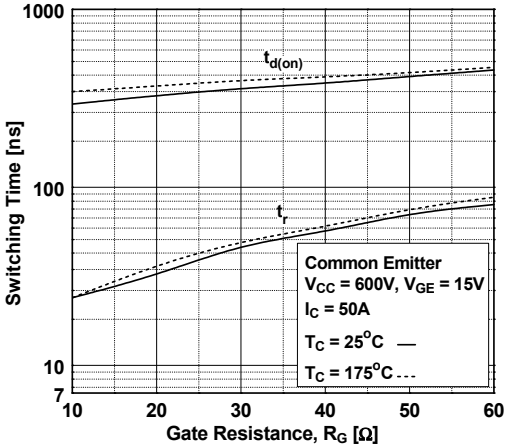
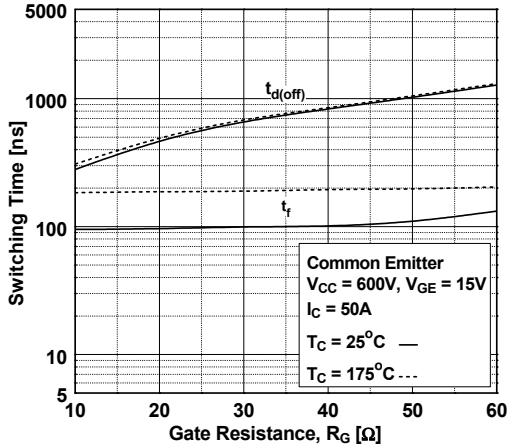


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

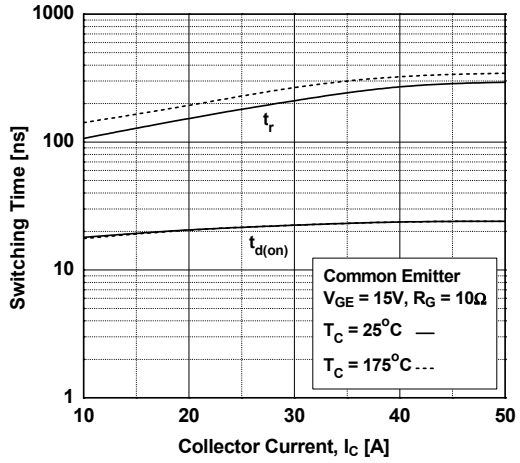


Figure 14. Turn-off Characteristics vs. Collector Current

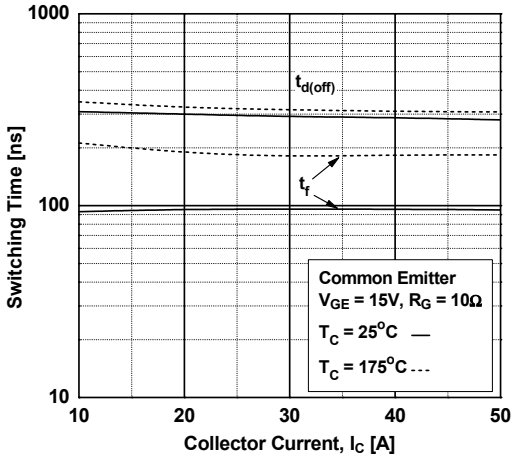


Figure 15. Switching Loss vs. Gate Resistance

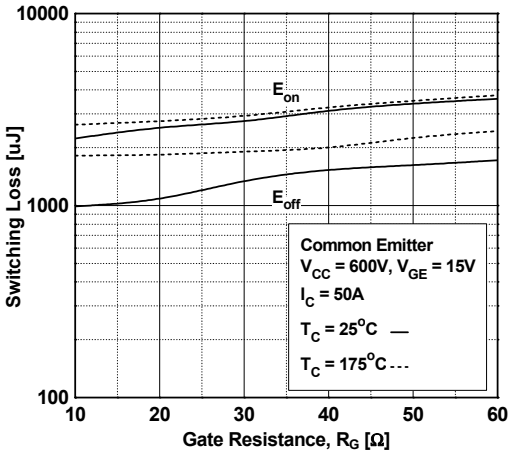


Figure 16. Switching Loss vs. Collector Current

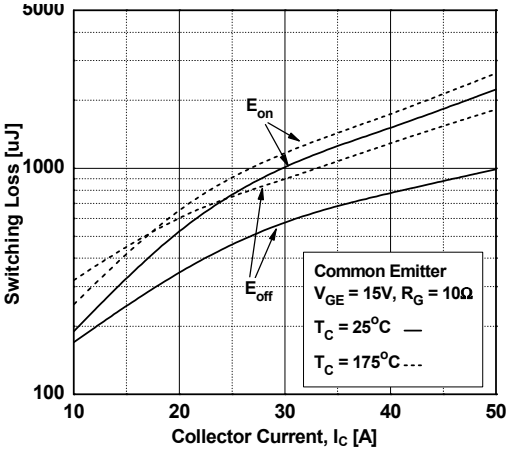


Figure 17. Turn off Switching SOA Characteristics

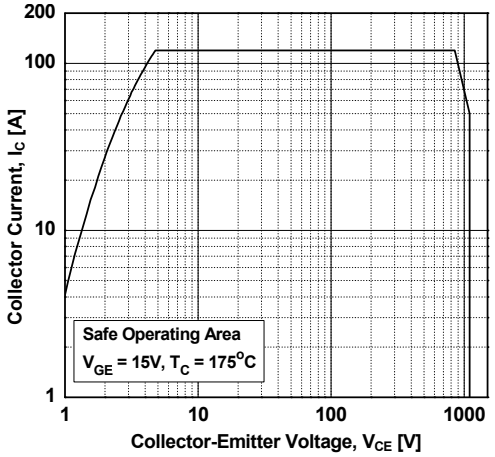
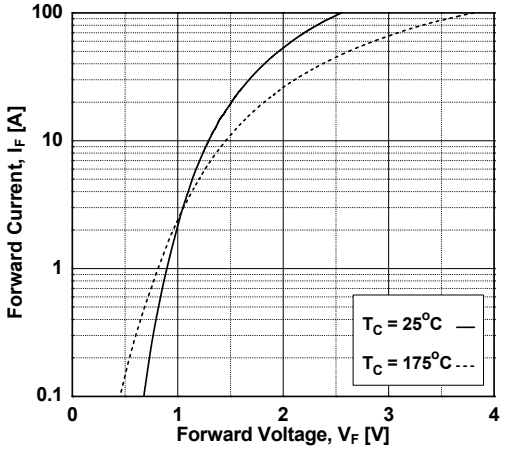
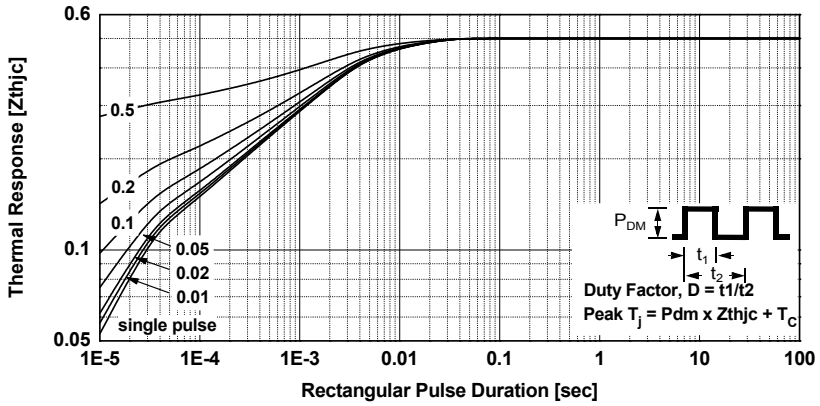


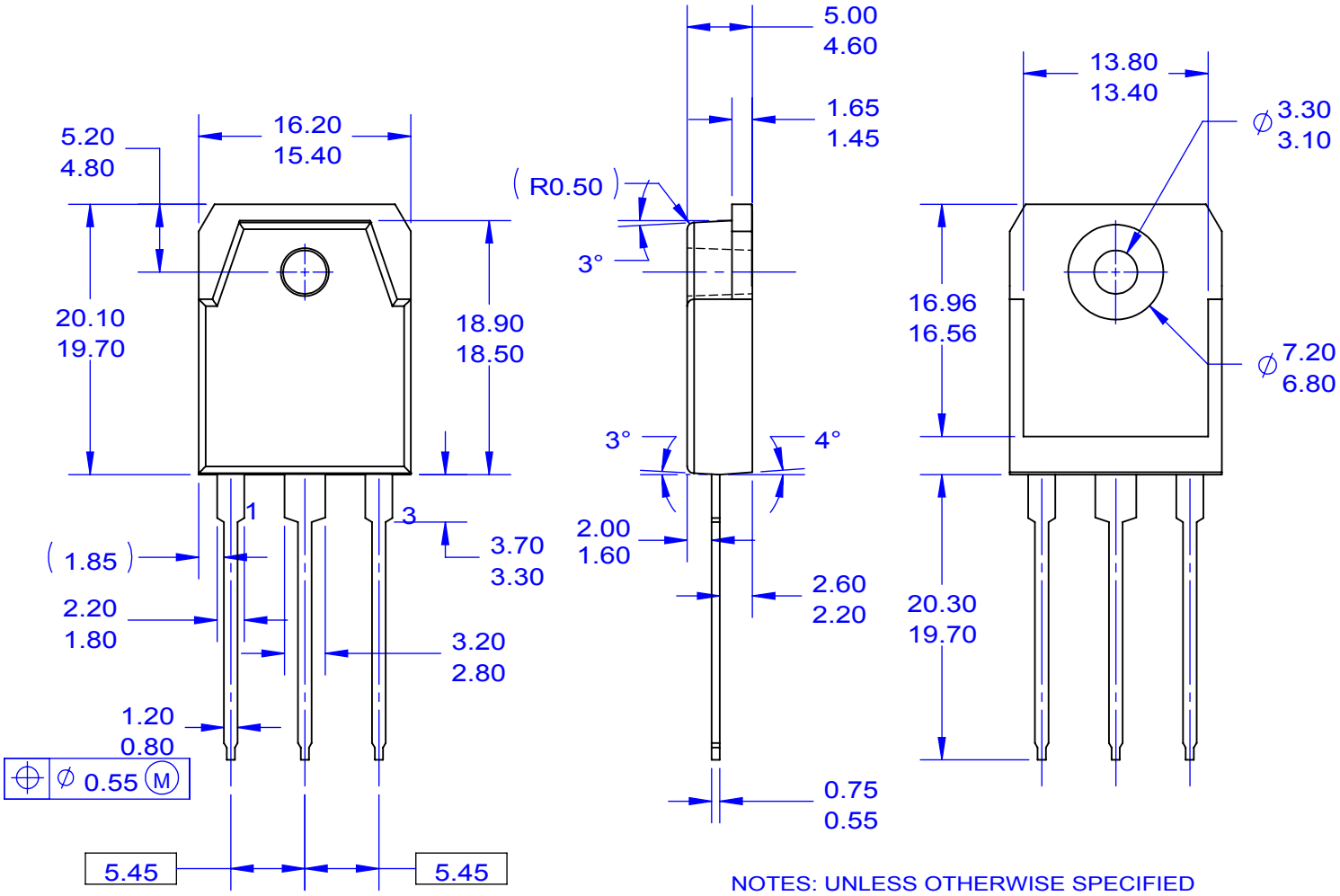
Figure 18. Forward Characteristics

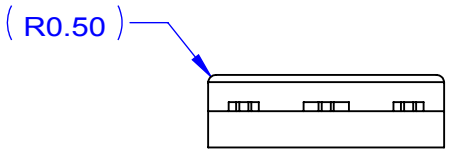


Typical Performance Characteristics

Figure 19. Transient Thermal Impedance of IGBT







NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
E) DRAWING FILE NAME: TO3PN03AREV2.
F) FAIRCHILD SEMICONDUCTOR.

FAIRCHILD ™

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative